K. J. Somaiya Institute of Technology, Sion, Mumbai-22 (Autonomous College Affiliated to University of Mumbai)

Nov - Dec 2024

Program: B.Tech. (Electronics and Telecommunication)Scheme IIB

KT Regular Examination: SY Semester: III

Course Code: EXC 303 and Course Name: Electronic Devices & Circuits

Date of Exam: 2 1/11/24 Duration: 02.5 Hours

Max. Marks: 60

Instructions:

(1)All questions are compulsory.

(2)Draw neat diagrams wherever applicable.

(3)Assume suitable data, if necessary.

Q. No.	Question	Max. Marks	СО	BT level
Q 1	Solve any two questions out of three: (05 marks each)	10		
a)	Explain differences between BJT and FET diode?		1	1
b)	Draw circuit diagram of BJT circuit with voltage divider biasing.		2	2
c)	Explain concept of DC load in line for the amplifier.		3	3
Q2	Solve any two questions out of three: (05 marks each)	10		ŧ
a)	What is biasing? And Explain need of biasing.		3	2
b)	State different types of Multistage amplifiers.		4	3
c)	Draw the circuit diagram of basic MOSFET differential amplifier and explain its operation.		6	3
Q.3	Solve any two questions out of three. (10 marks each)	20		
a)	Explain the effect of bypass capacitor and parasitic capacitor on frequency response of an amplifier		2	4
b)	Draw the circuit diagram and explain operation of two transistor current source. State its applications.		5	2
c)	Draw circuit diagram of class AB amplifier with diode biasing and explain its operation?		6	2
Q.4	Solve any two questions out of three. (10 marks each)	20		
a)	What is the function of power amplifiers? Explain its classification?		3	3

K. J. Somaiya Institute of Technology, Sion, Mumbai-22 (Autonomous College Affiliated to University of Mumbai)

Nov - Dec 2024

Program: B.Tech. (Electronics and Telecommunication)Scheme IIB

KT Regular Examination: SY Semester: III

Course Code: EXC 303 and Course Name: Electronic Devices & Circuits

Date of Exam: 21/11/24

Duration: 02.5 Hours

Max. Marks: 60

b)	What are different biasing circuits used for BJT ?Draw circuit diagram and explain the operation of any one biasing circuit for BJT ?	3	3
c)	(a) Z_i . (b) Z_o . (c) A_{vv}	1	4
	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		
	$h_{fe} = 120 Z_o$ $h_{ie} = 1.175 \text{ k}\Omega$ $h_{oe} = 20 \mu\text{A/V}$		
